

# EXHIBIT E

(12) **United States Patent**  
**Lee et al.**

(10) **Patent No.:** **US 8,252,675 B2**  
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(54) **METHODS OF FORMING CMOS TRANSISTORS WITH HIGH CONDUCTIVITY GATE ELECTRODES**

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(73) Assignee: **Samsung Electronics Co., Ltd.** (KR)

(\* ) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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(21) Appl. No.: **12/942,763**

*Primary Examiner* — Fernando L Toledo

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(65) **Prior Publication Data**

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(30) **Foreign Application Priority Data**

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(57) **ABSTRACT**

(51) **Int. Cl.**

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**H01L 21/44** (2006.01)  
**H01L 21/88** (2006.01)  
**H01L 21/4763** (2006.01)

Provided is a method for manufacturing a MOS transistor. The method comprises providing a substrate having a first active region and a second active region; forming a dummy gate stack on the first active region and the second active region, the dummy gate stack comprising a gate dielectric layer and a dummy gate electrode; forming source/drain regions in the first active region and the second active region disposed at both sides of the dummy gate stack; forming a mold insulating layer on the source/drain region; removing the dummy gate electrode on the first active region to form a first trench on the mold insulating layer; forming a first metal pattern to form a second trench at a lower portion of the first trench, and removing the dummy gate electrode on the second active region to form a third trench on the mold insulating layer; and forming a second metal layer in the second trench and the third trench to form a first gate electrode on the first active region and a second gate electrode on the second active region.

(52) **U.S. Cl.** ..... **438/592**; 438/299; 438/637; 438/926; 438/183; 257/E21.177; 257/E21.621; 257/E21.626; 257/E21.64

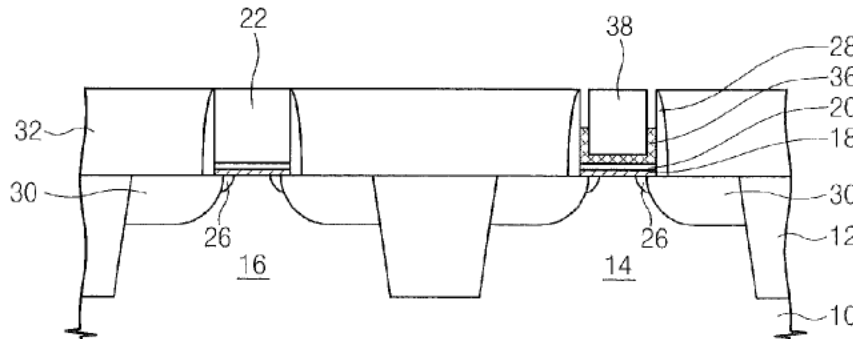
(58) **Field of Classification Search** ..... 438/296  
 See application file for complete search history.

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**15 Claims, 19 Drawing Sheets**



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Fig. 1

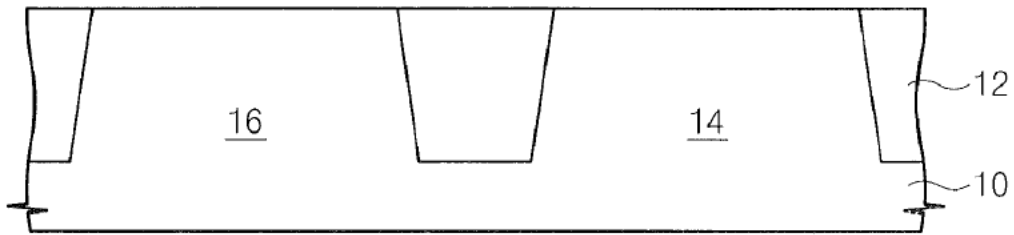


Fig. 2

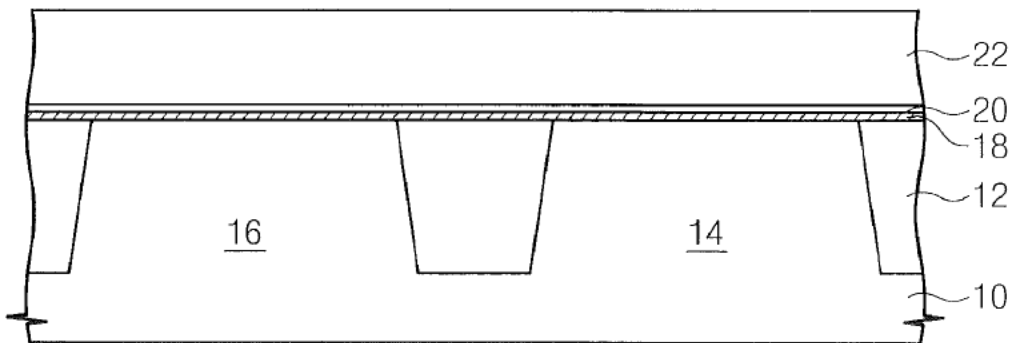


Fig. 3

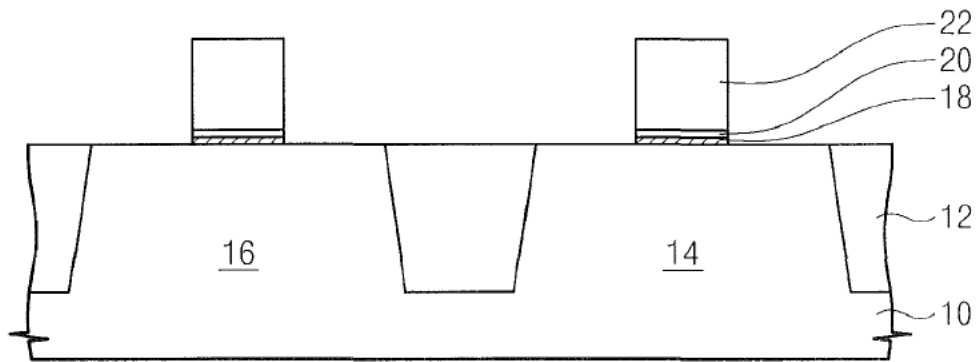
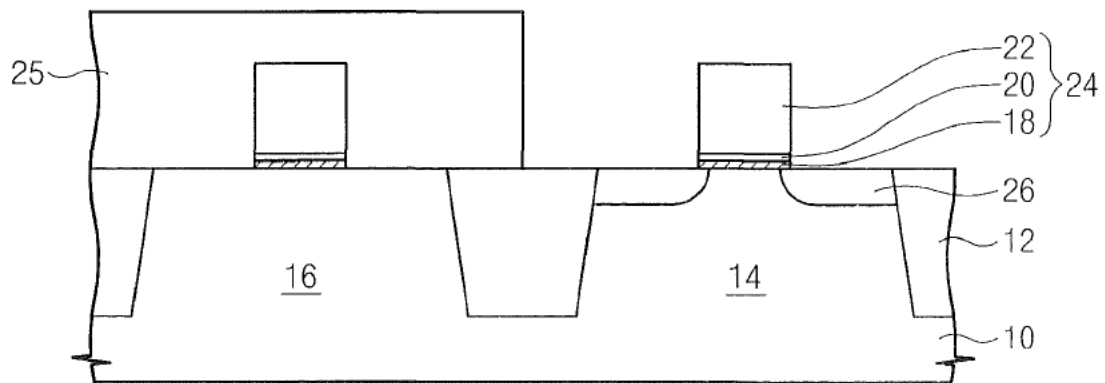


Fig. 4



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